

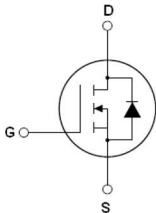
N-Channel Super Junction Power MOSFET III

General Description

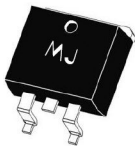
The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

- ◆ New technology for high voltage device
- ◆ Low on-resistance and low conduction losses
- ◆ Small package
- ◆ Ultra Low Gate Charge cause lower driving requirements
- ◆ 100% Avalanche Tested
- ◆ ROHS compliant



Schematic diagram



TO-263

Application

- ◆ Power factor correction (PFC)
- ◆ Switched mode power supplies(SMPS)
- ◆ Uninterruptible Power Supply (UPS)

V_{DS}	800	V
$R_{DS(ON)MAX}$	900	mΩ
I_D	6	A

Package Marking And Ordering Information

Device	Device Package	Marking
MJ80T900D	TO-263	MJ80T900D

Table 1. Absolute Maximum Ratings (Tc=25℃)

Parameter	Symbol	MJ80T900D	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	800	V
Gate-Source Voltage ($V_{DS}=0V$) ,AC ($f>1\text{ Hz}$)	V_{GS}	±30	V
Continuous Drain Current at Tc=25℃	I_D (DC)	6	A
Continuous Drain Current at Tc=100℃	I_D (DC)	3.8	A
Pulsed drain current ^(Note 1)	I_{DM} (pluse)	24	A
Maximum Power Dissipation (Tc=25℃)	P_D	98	W
Derate above 25℃	P_D	0.78	W/℃
Single pulse avalanche energy ^(Note 2)	E_{AS}	100	mJ
Avalanche current ^(Note 1)	I_{AR}	5	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} ^(Note 1)	E_{AR}	0.3	mJ

Parameter	Symbol	MJ80T900D	Unit
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	℃

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	MJ80T900D	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R _{thJC}	1.28	°C/W
Thermal Resistance, Junction-to-Ambient (Maximum)	R _{thJA}	62	°C/W

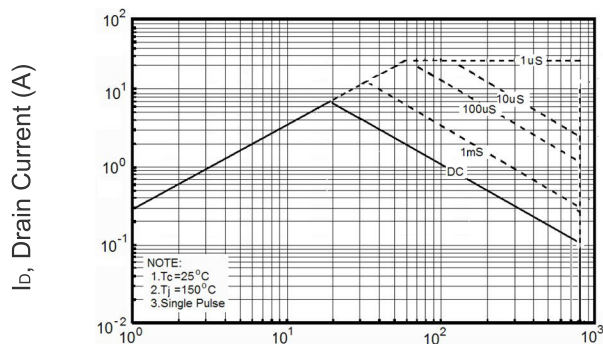
Table 3. Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	800	-	-	V
Zero Gate Voltage Drain Current (Tc=25°C)	I _{DSS}	V _{DS} =800V,V _{GS} =0V	-	-	1	μA
Zero Gate Voltage Drain Current (Tc=125°C)	I _{DSS}	V _{DS} =800V,V _{GS} =0V	-	-	100	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	3	3.5	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =4A	-	750	900	mΩ
Dynamic Characteristics						
Forward Transconductance	g _{FS}	V _{DS} =20V,I _D =4A	-	6	-	S
Input Capacitance	C _{ies}	V _{DS} =50V,V _{GS} =0V F=1.0MHz	-	1320	-	pF
Output Capacitance	C _{oss}		-	33	-	pF
Reverse Transfer Capacitance	C _{rss}		-	2	-	pF
Total Gate Charge	Q _g	V _{DS} =640V,I _D =6A V _{GS} =10V	-	22.8	-	nC
Gate-Source Charge	Q _{gs}		-	7.7	-	nC
Gate-Drain Charge	Q _{gd}		-	6.9	-	nC
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =400V,I _D =3A R _G =3Ω,V _{GS} =10V	-	10	-	nS
Turn-on Rise Time	t _r		-	5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	53	70	nS
Turn-Off Fall Time	t _f		-	6	9	nS
Source- Drain Diode Characteristics						
Source-drain current (Body Diode)	I _{SD}	T _C =25°C	-	-	6	A
Pulsed Source-drain current (Body Diode)	I _{SDM}		-	-	24	A
Forward On Voltage	V _{SD}	T _J =25°C,I _{SD} =6A,V _{GS} =0V	-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _J =25°C,I _F =3A di/dt=100A/μs	-	260	-	nS
Reverse Recovery Charge	Q _{rr}		-	1.7	-	uC
Peak reverse recovery Current	I _{rrm}		-	13	-	A

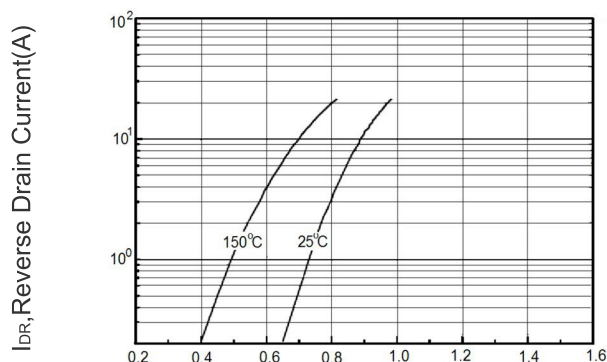
Notes

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature
2. $T_J=25^{\circ}\text{C}$, $V_{DD}=50\text{V}$, $V_G=10\text{V}$, $R_G=25\Omega$

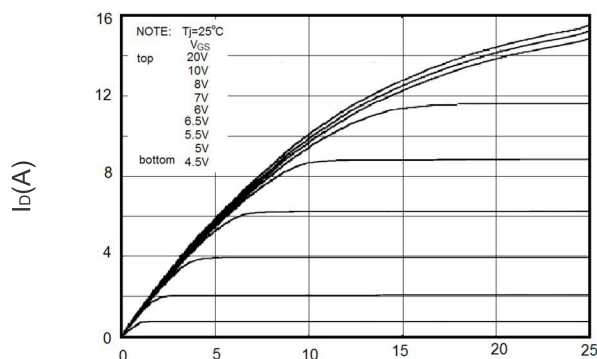
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)



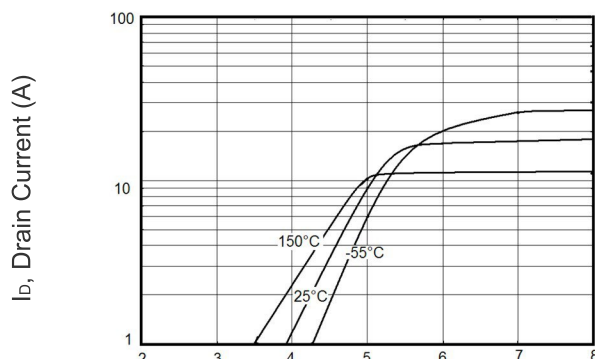
V_{DS} , Drain-Source Voltage (V)
Figure 1 Safe operating area



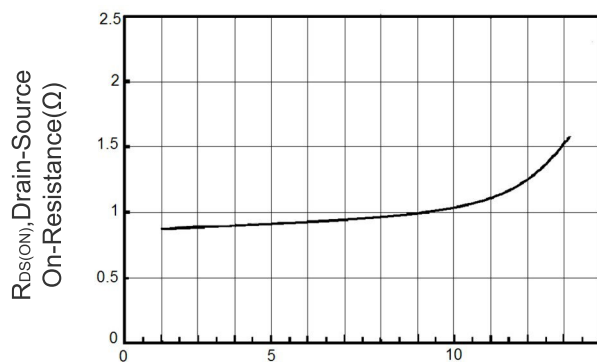
V_{SD} , Source-Drain Voltage (V)
Figure 2 Source-Drain Diode Forward Voltage



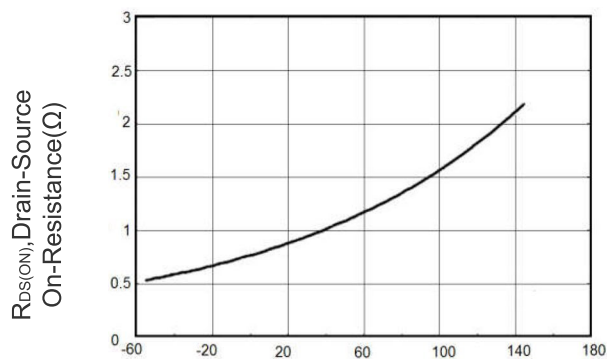
V_{DS} (V)
Figure 3 Output characteristics



V_{GS} , Gate-Source Voltage (V)
Figure 4 Transfer characteristics



I_D , Drain Current (A)
Figure 5 Static drain-source on resistance



T_J , Junction Temperature ($^{\circ}\text{C}$)
Figure 6 $R_{DS(ON)}$ vs Junction Temperature

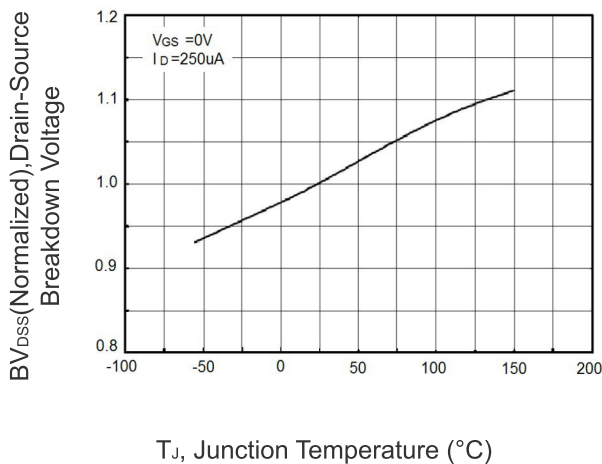


Figure 7 BV_{DS} vs Junction Temperature

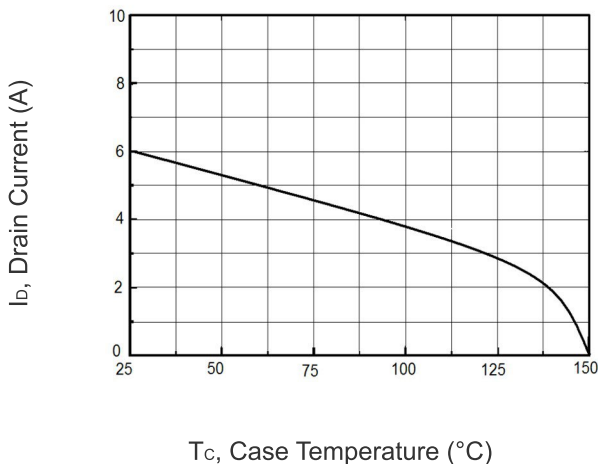


Figure 8 Maximum I_D vs Junction Temperature

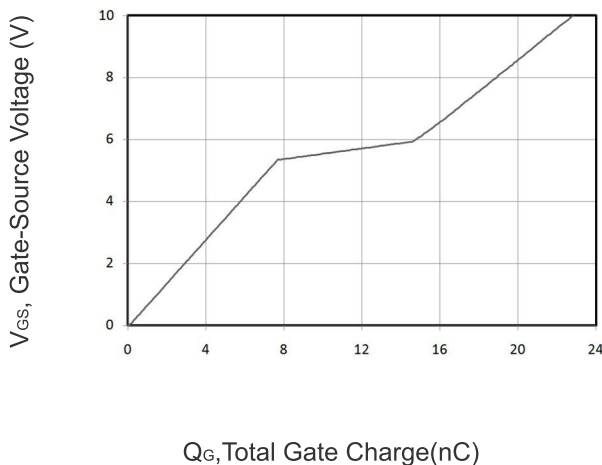


Figure 9 Gate charge waveforms

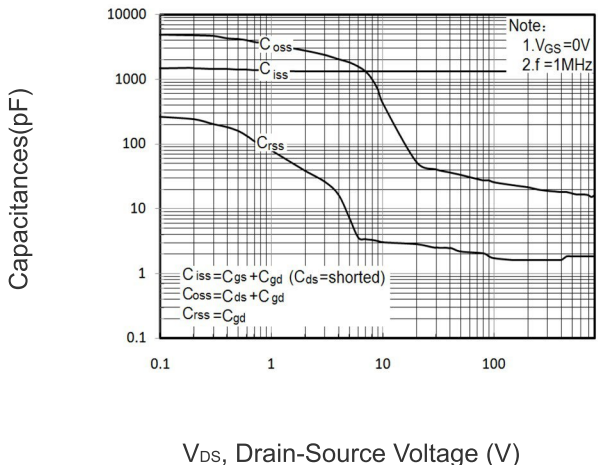


Figure 10 Capacitance

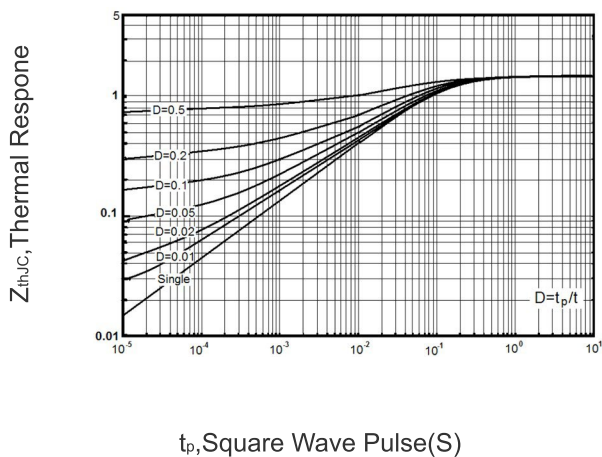
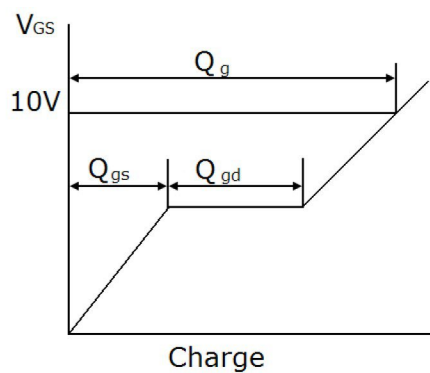
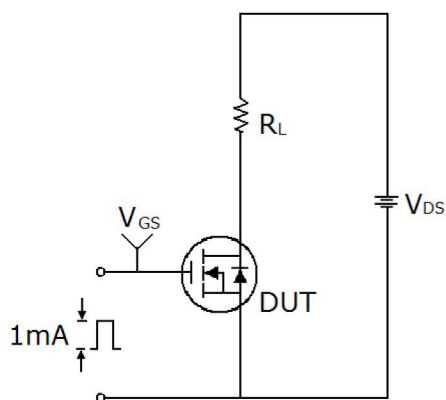
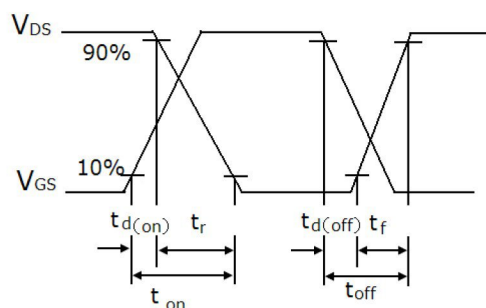
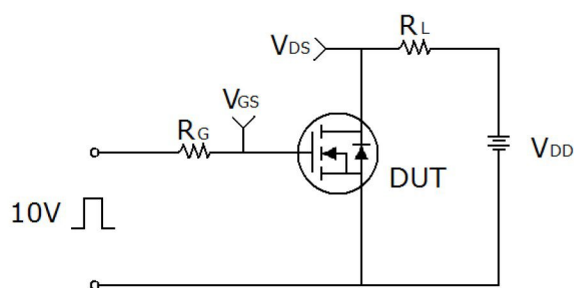


Figure 11 Transient Thermal Impedance

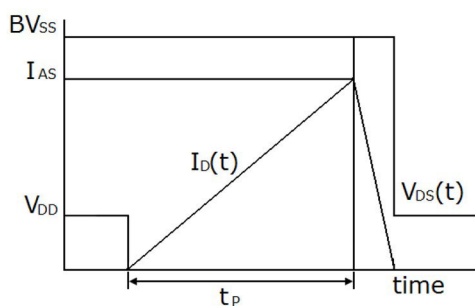
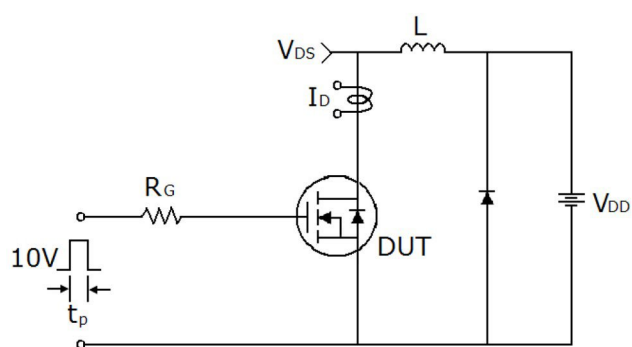
Test circuit



Gate charge test circuit & Waveform

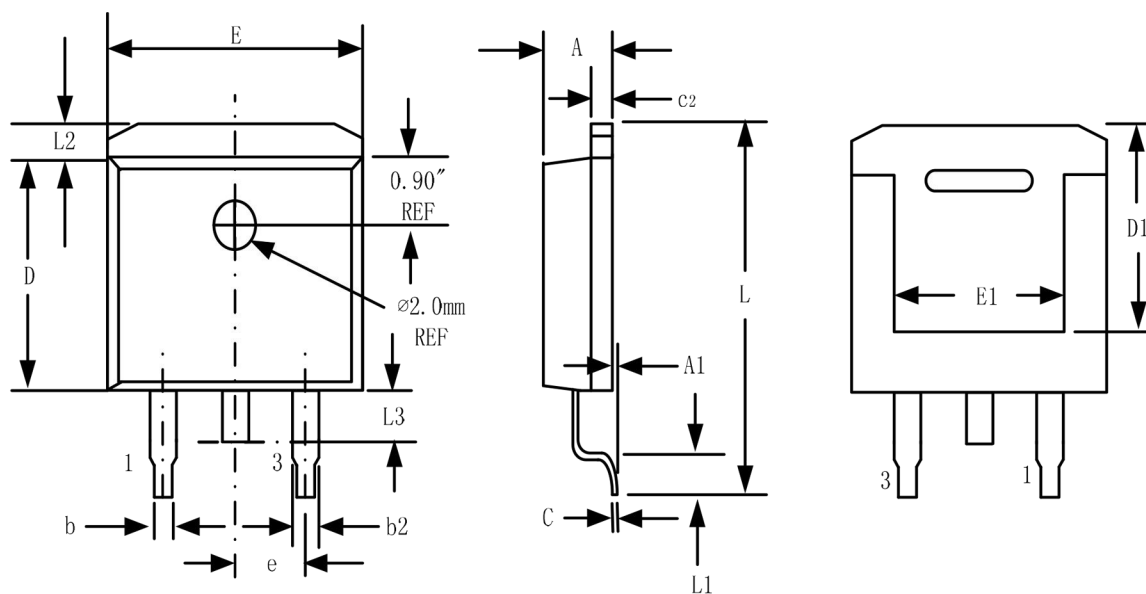


Switch Time Test Circuit



Unclamped Inductive Switching Test Circuit & Waveforms

TO-263-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.57	0.170	0.180
A1	-	0.25		0.010
b	0.71	0.94	0.028	0.037
b2	1.15	1.40	0.045	0.055
c	0.46	0.61	0.018	0.024
c2	1.22	1.40	0.048	0.055
D	8.89	9.40	0.350	0.370
D1	8.01	8.23	0.315	0.324
E	10.04	10.28	0.395	0.405
E1	7.88	8.08	0.310	0.318
e	2.54 BSC		0.100 BSC	
L	14.73	15.75	0.580	0.620
L1	2.29	2.79	0.090	0.110
L2	1.15	1.39	0.045	0.055
L3	1.27	1.77	0.050	0.070

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